

PIMD3-Q

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

1 August 2025

Product data sheet

1. General description

NPN/PNP Resistor-Equipped Transistors (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	er transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
R1	bias resistor 1 (input)			7	10	13	kΩ	
R2/R1	bias resistor ratio			0.8	1	1.2		



50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0 	TR1 R2 R1
6	O1	output (collector) TR1	TSOP6 (SOT457)	GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PIMD3-Q	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMD3-Q	м7

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	h negative polarity	'			
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	10	V
V _I	input voltage	input voltage TR1		-	40	V
				-	-10	V
		input voltage TR2		-	10	V
				-	-40	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
Per device			'		<u>'</u>	_
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

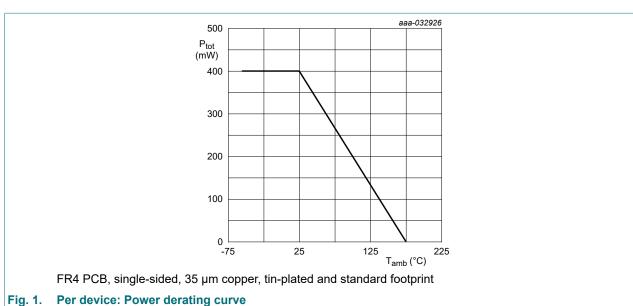


Fig. 1.

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	313	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

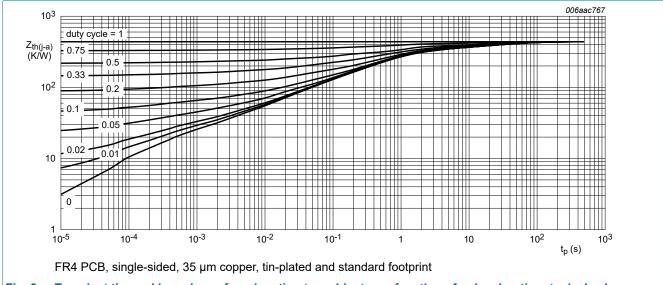


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

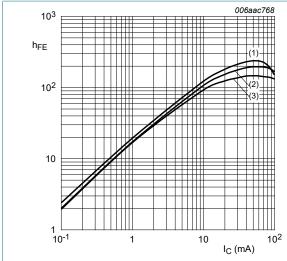
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		50	-	-	V
I _{СВО}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	400	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	1.1	0.8	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 10 mA; T _{amb} = 25 °C		2.5	1.8	-	V
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
TR1 (NPN)							
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[1]	-	230	-	MHz
TR2 (PNP)							,
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[1]	-	180	-	MHz

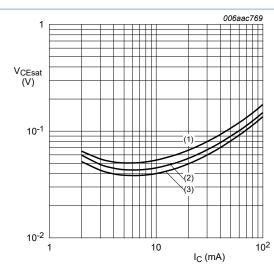
^[1] Characteristics of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω



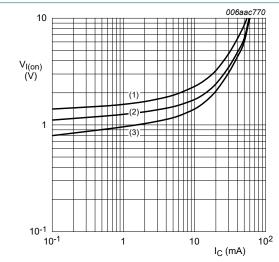
V_{CE} = 5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

TR1 (NPN): Collector-emitter saturation voltage Fig. 4. as a function of collector current; typical values



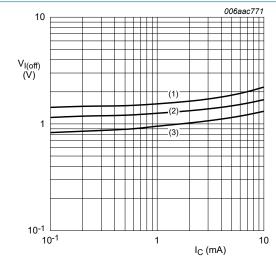
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 kΩ, R2 = 10 kΩ

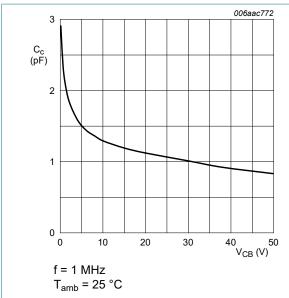
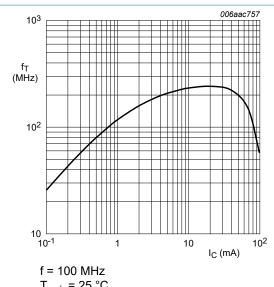
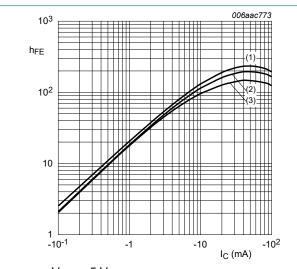


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



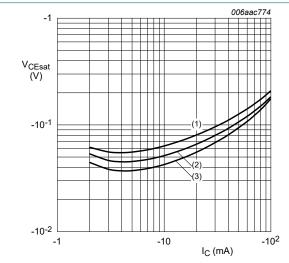
f = 100 MHz $T_{amb} = 25 ^{\circ}\text{C}$ $V_{CE} = 5 \text{ V}$

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

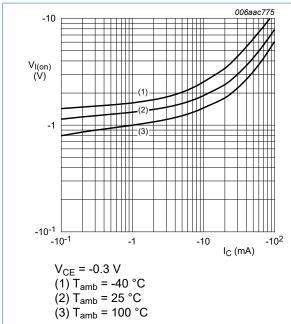
Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values

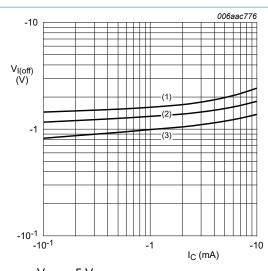


 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = -40~{\rm ^{\circ}C}$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω





V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

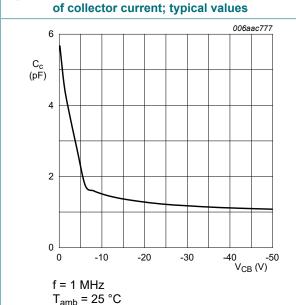
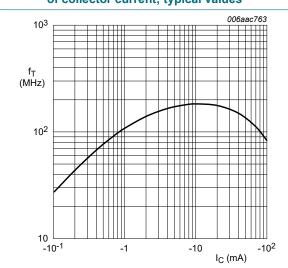


Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz T_{amb} = 25 °C $V_{CE} = -5 V$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

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50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

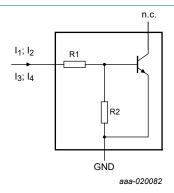


Fig. 15. NPN transistor: Resistor test circuit

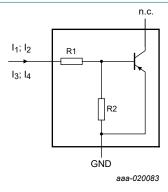


Fig. 16. PNP transistor: Resistor test circuit

Resistor test conditions

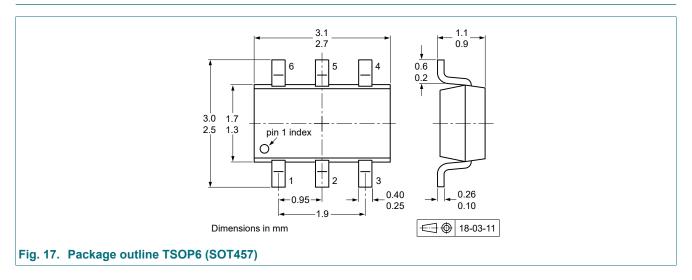
Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

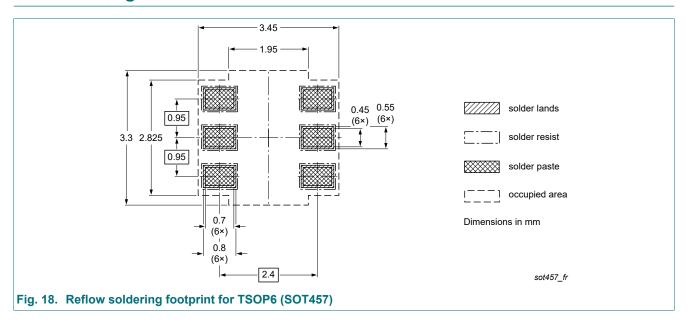
Product	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	l ₂	l ₃	14
PIMD3-Q	10	10	350 μΑ	450 µA	-350 μΑ	-450 μA

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

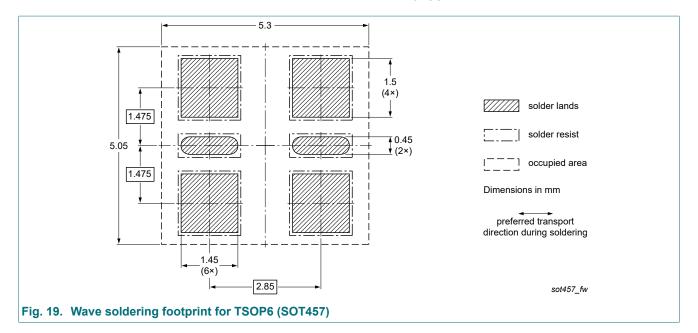
12. Package outline



13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 kΩ, R2 = 10 kΩ



50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 k Ω , R2 = 10 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMD3-Q v.1	20250801	Product data sheet	-	-

50 V, 100 mA NPN/PNP resistor-equipped transistor; R1 = 10 kΩ, R2 = 10 kΩ

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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